

## JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

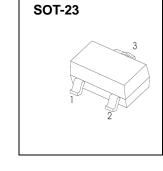
## **SOT-23 Plastic-Encapsulate Diodes**

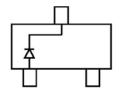
### BAS40/-04/-05/-06

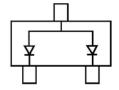
#### SCHOTTKY BARRIER DIODE

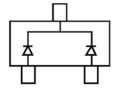
#### **FEATURES**

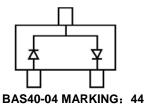
- Low Forward Voltage
- Fast Switching











BAS40 MARKING: 43•

**BAS40-06 MARKING: 46** 

**BAS40-05 MARKING: 45** 

Maximum Ratings @Ta=25℃

Parameter	Symbol	Limit	Unit
Peak repetitive peak reverse voltage	$V_{RRM}$		
Working peak reverse voltage	$V_{RWM}$	40	V
DC blocking voltage	$V_R$		
Forward continuous current	I <sub>FM</sub>	200	mA
Power dissipation	P <sub>D</sub>	200	mW
Thermal resistance junction to ambient	$R_{\theta JA}$	500	°C/W
Junction temperature	TJ	125	°C
Storage temperature range	T <sub>STG</sub>	-55~+150	°C

#### **ELECTRICAL CHARACTERISTICS (Ta=25℃ unless otherwise specified)**

Parameter	Symbol	Test conditions	Min	Max	Unit
Reverse breakdown voltage	V <sub>(BR)</sub>	I <sub>R</sub> = 10µA	40		V
Reverse voltage leakage current	I <sub>R</sub>	V <sub>R</sub> =30V		200	nA
Forward voltage	V <sub>F</sub>	I <sub>F</sub> =1mA I <sub>F</sub> =40mA		380 1000	mV
Diode capacitance	C <sub>D</sub>	V <sub>R</sub> =0,f=1MHz		5	pF
Reverse recovery time	t <sub>rr</sub>	$I_{rr}$ =1mA, $I_{R}$ = $I_{F}$ =10mA $R_{L}$ =100 $\Omega$		5	ns

# **Typical Characteristics**

## BAS40/-04/-05/-06

